

TYN612M

12 A SCR

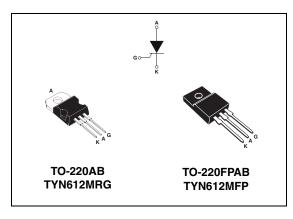
Main features

Symbol	Value	Unit
I _{T(RMS)}	12	А
V _{DRM} /V _{RRM}	600	V
I _{GT} (min / max)	1.5 / 5	mA

Description

The TYN612M SCR is suitable to fit modes of control found in applications such as voltage regulation circuits for motorbikes, overvoltage crowbar protection, motor control circuits in power tools and kitchen aids, inrush current limiting circuits, capacitive discharge ignition.

The insulated fullpack package allows a back to back configuration.



Order codes

Part Numbers	Marking
TYN612MRG	TYN612M
TYN612MFP	TYN612MFP

Symbol	Param	Value	Unit			
1	RMS on-state current	TO-220AB		12	۸	
I _{T(RMS)}	(180° conduction angle)	TO-220FPAB	$T_c = 70^\circ C$	12	A	
1	Average on-state current	TO-220AB	$T_c = 105^\circ C$	8	A	
I _{T(AV)}	(180° conduction angle)	TO-220FPAB	$T_c = 70^\circ C$	8		
1	Non repetitive surge peak on-state	t _p = 8.3 ms	T 25° C	125	А	
ITSM	current	t _p = 10 ms	$T_{j} = 25^{\circ} C$	120		
l²t	I ² t Value for fusing	t _p = 10 ms	$T_j = 25^\circ C$	72	A ² s	
dl/dt	Critical rate of rise of on-state current $I_G = 2 \; x \; I_{GT}$, $t_r \leq 100 \; ns$	F = 60 Hz	T _j = 125° C	50	A/µs	
I _{GM}	Peak gate current	t _p = 20 μs	$T_j = 125^\circ C$	4	А	
P _{G(AV)}	Average gate power dissipation	·	T _j = 125° C	1	W	
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C	
V _{RGM}	Maximum peak reverse gate voltage			5	V	

 Table 1.
 Absolute ratings (limiting values)

April 2007

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1 Characteristics

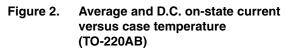
Symbol	Test Con		Value	Unit	
1	$V_{D} = 12 V$ $R_{I} = 140 \Omega$	MIN.	1.5	mA	
I _{GT}	$v_{\rm D} = 12$ $v_{\rm DL} = 140.32$		MAX.	5	- IIIA
			MIN.	0.5	V
V _{GT}	$V_D = 12 V$ $R_L = 140 \Omega$		TYP.	0.7	
		MAX.	1.3		
V _{GD}	$V_{D} = V_{DRM} R_{L} = 3.3 \text{ k}\Omega \qquad \qquad T_{j} = 125^{\circ} \text{ C}$		MIN.	0.2	V
Ι _Η	I _T = 500 mA Gate open	MAX.	20	mA	
١L	$I_{G} = 1.2 I_{GT}$		MAX.	40	mA
dV/dt	$V_D = 67 \% V_{DRM}$ Gate open	$T_j = 125^\circ C$	MIN.	50	V/µs
V _{TM}	I _{TM} = 24 A t _p = 380 μs	$T_j = 25^\circ C$	MAX.	1.6	V
V _{t0}	Threshold voltage	$T_{j} = 125^{\circ} C$	MAX.	0.85	V
R _d	Dynamic resistance $T_j = 125^{\circ} C$		MAX.	30	mΩ
I _{DRM}	$T_j = 25^\circ C$		MAX.	5	μΑ
I _{RRM}	$V_{DRM} = V_{RRM}$	$T_j = 125^\circ C$		2	mA

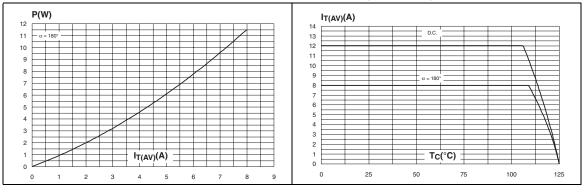
Table 2. Electrical characteristics ($T_i = 25^\circ C$, unless otherwise specified)

Table 3. Thermal resistance

Symbol	Parameter			Unit	
Р	lunction to coop (DC)	TO-220AB	1.3	° C AAI	
R _{th(j-c)}	Junction to case (DC)	TO-220FPAB	4.5	° C/W	
D	Junction to ambient (DC)	TO-220AB	55	° C/W	
R _{th(j-a)}		TO-220FPAB	55	- ° C/W	

Figure 1. Maximum average power dissipation versus average on-state current



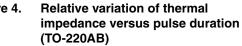


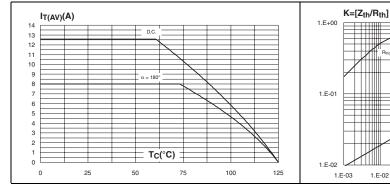
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Figure 3. Average and D.C. on-state current Figure 4. versus case temperature (TO-220FPAB)

TYN612M





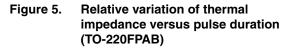


Figure 6. Relative variation of gate trigger current, holding current, latching current and gate trigger voltage versus junction temperature (typical values)

1.E-01

t_p(s)

1.E+00

1.E+01

1.E+02

1.E+03

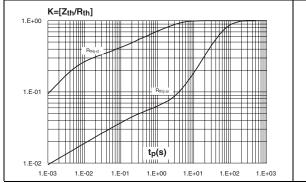
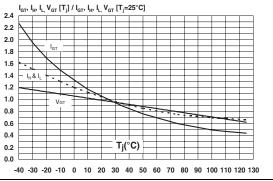
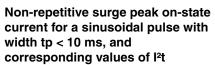
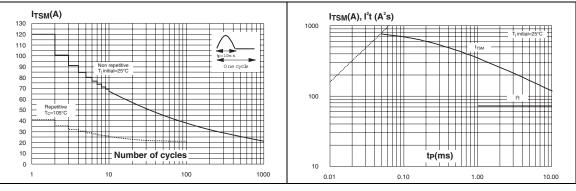


Figure 7. Surge peak on-state current versus Figure 8. number of cycles







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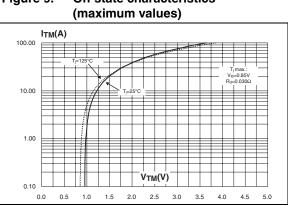
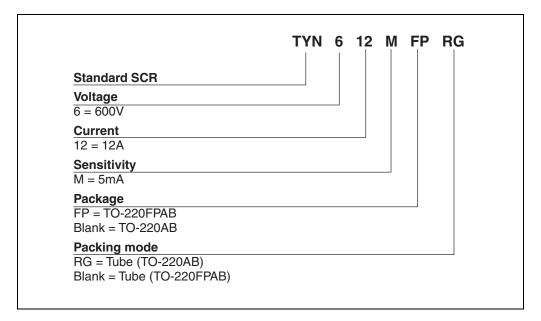


Figure 9. **On-state characteristics**

Ordering information scheme 2



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3 Package information

• Epoxy meets UL94, V0

Table 4. TO-220AB dimensions

					Dimer	nsions		
		Ref. M	Mi	Millimeters		Inches		
			Min.	Тур.	Max.	Min.	Тур.	Max.
	b2	Α	15.20		15.90	0.598		0.625
в		a1		3.75			0.147	
		a2	13.00		14.00	0.511		0.551
		В	10.00		10.40	0.393		0.409
	C2 C2	b1	0.61		0.88	0.024		0.034
A		b2	1.23		1.32	0.048		0.051
14 13 · - (小-		С	4.40		4.60	0.173		0.181
		c1	0.49		0.70	0.019		0.027
		c2	2.40		2.72	0.094		0.107
		е	2.40		2.70	0.094		0.106
		F	6.20		6.60	0.244		0.259
j ↓ t t t t t t t t t t t t t t t t t t	M ← c1	ØI	3.75		3.85	0.147		0.151
e '		14	15.80	16.40	16.80	0.622	0.646	0.661
		L	2.65		2.95	0.104		0.116
		12	1.14		1.70	0.044		0.066
		13	1.14		1.70	0.044		0.066
		М		2.60			0.102	



			Dimer	nsions	
	Ref.	Millim	neters	Inches	
		Min.	Max.	Min.	Max.
	А	4.4	4.6	0.173	0.181
	В	2.5	2.7	0.098	0.106
	D	2.5	2.75	0.098	0.108
	Е	0.45	0.70	0.018	0.027
Dia	F	0.75	1	0.030	0.039
	F1	1.15	1.70	0.045	0.067
L2 L7	F2	1.15	1.70	0.045	0.067
	G	4.95	5.20	0.195	0.205
	G1	2.4	2.7	0.094	0.106
	Н	10	10.4	0.393	0.409
L4	L2	16 Тур.		0.63 Тур.	
↓↓₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩	L3	28.6	30.6	1.126	1.205
G1 ↔	L4	9.8	10.6	0.386	0.417
G	L5	2.9	3.6	0.114	0.142
	L6	15.9	16.4	0.626	0.646
	L7	9.00	9.30	0.354	0.366
	Dia.	3.00	3.20	0.118	0.126

Table 5. TO-220FPAB Dimension

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

4 Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
TYN612MRG	TYN612M	TO-220AB	2.3 g	50	Tube
TYN612MFP	TYN612MFP	TO-220AB	2.0 g	50	Tube

5 Revision history

Date	Revision	Description of Changes
Sep-2002	1A	Last update.
10-Fev-2005	2	TO-220FPAB package added.
11-Apr-2007	3	Reformatted to current standards. Added typical and minimum values for V_{GT} in <i>Table 2</i> .
17-Apr-2007	4	Added V _{GT} curve in <i>Figure 6</i> .



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